

Sheet 1 of 1

Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE	ATTY DOCKET NO. 126961	APPLICATION NO. 10/558186 New U.S. National Stage of PCT/JP2004/011685
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANTS Izumi FUSEGAWA et al.		
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U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number	Date	Name
F.H.	1.	2003/0116082 A1	06/26/2003	Masahiro SAKURADA et al.
F.H.	2.	2002/0157600 A1	10/31/2002	Izumi FUSEGAWA et al.

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation
F.H.	3.	JP-A-2002-201093	07/16/2002	JAPAN	X	X
1	4.	WO 01/63027 A1	08/30/2001	WIPO	X	
	5.	WO 01/81661 A1	11/01/2001	WIPO	X	
	6.	JP-A-09-202684	08/05/1997	JAPAN	X	X
	7.	JP-A-07-041383	02/10/1995	JAPAN	X	X
✓	8.	JP-A-08-330316	12/13/1996	JAPAN	X	X
✓	9.	JP-A-11-147786	06/02/1999	JAPAN	X	X
F.H.	10.	JP-A-2000-327485	11/28/2000	JAPAN	X	X

OTHER DOCUMENTS

Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)
F.H.	11.	Makoto TAKIYAMA et al.; "Dielectric Degradation of Silicon Dioxide Films Cased by Metal Contaminations"; <i>Ultra Clean Technology</i> ; Vol. 5, No. 5/6; Nippon Steel Corporation; pp. 345-359. (with abstract)

EXAMINER

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Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.